



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **WATANABE, et al.**

Serial No.: **09/320,271**

Filed: **May 27, 1999**

Group Art Unit: **2825**

Examiner: **LEE**

P.T.O. Confirmation No.: **4409**

For: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

RESPONSE UNDER 37 CFR §1.116
- EXPEDITED RESPONSE -
GROUP ART UNIT 2825

BOX AF

Commissioner for Patents
Washington, D.C. 20231

March 17, 2003

Sir:

In response to the Office Action dated **December 16, 2002**, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 1 as follows:

- FT 1. (Five Times Amended) A fabrication method of a semiconductor device comprising the steps of:
forming a first insulation layer on a flat underlying face over a substrate,
introducing impurities into said first insulation layer, and
embedding and forming a first conductive layer in said first insulation layer by the Damascene method.

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paper
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#1